NSN 5961-00-765-4589

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Inclosure Material:
Metal
Overall Length:
0.260 inches
Terminal Length:
0.500 inches
Overall Diameter:
0.370 inches
Component Name And Quantity:
2 transistor
Mounting Method:
Terminal
Terminal Circle Diameter:
0.200 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
100.0 collector to base voltage/static/emitter open all transistor and 7.0 emitter to base voltage, static, collector open all transistor and 60.0
collector to emitter voltage/static/base open all transistor
Current Rating Per Characteristic:
500.00 milliamperes source cutoff current all transistor
Power Rating Per Characteristic:
2.1 watts small-signal input power, common-collector preset all transistor
Transfer Ratio:
75.0 static forward current transfer ratio, common-emitter all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
All transistor junction pattern arrangement: npn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
6 uninsulated wire lead
Specification Data:
81349-mil-s-19500/270 government specification
Shelf Life:
N/a
Unit Of Measure:

N

Demilitarization:

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